

Revision 0.91

SINGLE FREQUENCY LASER DIODES Distributed Feedback Laser



General Product Information

Product	Application
Tunable 780 nm DFB Laser	Spectroscopy
with hermetic 14-Pin Butterfly Housing (RoHS compliant)	Metrology
including Monitor Diode, Thermoelectric Cooler and Thermistor	THz Generation
with integrated Beam Collimation	



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T_{S}	°C	-40		85
Operational Temperature at Case	T_{C}	°C	-40		85
Operational Temperature at Laser Chip	T_{LD}	°C	10		50
Forward Current	I _F	mA			190
Reverse Voltage	V_R	V			2
Output Power	P_{opt}	mW			90
TEC Current	I _{TEC}	А			1.1
TEC Voltage	V_{TEC}	V			2.8

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T_{case}	°C	-20		65
Operational Temperature at Laser Chip	T_{LD}	°C	15		45
Forward Current	I _F	mA			180
Output Power	P_{opt}	mW	20		80

Measurement Conditions / Comments	
measured by integrated Thermistor	

Characteristics at T_{LD} = 25° C at BOL

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	779	780	781
Linewidth (FWHM)	Δλ	MHz		2	
Mode-hop free Tuning Range	$\Delta \lambda_{\text{tune}}$	pm		1500	
Sidemode Supression Ratio	SMSR	dB	30	50	
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.06	
Current Coefficient of Wavelength	dλ / dl	nm / mA		0.003	

see images on page 4	
$P_{opt} = 80 \text{ mW}$	
reached by temperature modulation	
$P_{opt} = 80 \text{ mW}$	



Revision 0.91

SINGLE FREQUENCY LASER DIODES Distributed Feedback Laser



Characteristics at T_{LD} = 25° C	at BOL				cont'd
Parameter	Symbol	Unit	min	typ	max
Mode-hop free Temperature Range	T_{LD}	° C	15		40
Mode-hop free Power Range	P_{opt}	mW	20		80
Laser Current @ P _{opt} = 80 mW	I_{LD}	mA			180
Slope Efficiency	η	W/A	0.6	0.8	1.1
Threshold Current	I _{th}	mA			70
Divergence parallel (FWHM)	$\Theta_{ }$	0		0.1	
Divergence perpendicular (FWHM)	Θ_{\perp}	0		0.1	
Beam Diameter horizontal (1/e²)	d	mm		1.0	1.2
Beam Diameter vertical (1/e ²)	d.	mm		0.8	1.2

Measurement Conditions / Comments
The data of the first contained by Comments
Temperature at Laser Chip
parallel to the base plate of the housing (see p. 3)
perpendicular to base plate of the housing (see p. 3)
parallel to the base plate of the housing (see p. 3)
perpendicular to base plate of the housing (see p. 3)

Monitor Diode					
Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{opt}	μA/mW	1		20

Meas	urement Conditions / Comments
$J_R =$	5 V

Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	А		0.4	
Voltage	U_TEC	V		1.3	
Power Dissipation (total loss at case)	P _{loss}	W		0.5	
Temperature Difference	ΔΤ	K			50

Measurement Conditions / Comments
$P_{opt} = 80 \text{ mW}, \Delta T = 20 \text{ K}$
$P_{opt} = 80 \text{ mW}, \Delta T = 20 \text{ K}$
$P_{opt} = 80 \text{ mW}, \Delta T = 20 \text{ K}$
$P_{opt} = 80 \text{ mW}, \Delta T = Tcase - TLD $
орт , , ,

Symbol	Unit	min	typ	max
R	kΩ		10	
β			3892	
А			1.1293 x 10)-3
В		2.3410 x 10 ⁻⁴		
C			8.7755 x 10)-8
	R β A	R kΩ β A	R kΩ β A B	R kΩ 10 β 3892 A 1.1293 x 10

Measurement Conditions / Comments						
$T_{LD} = 25^{\circ} C$						
$R_1/R_2 = e^{\beta(1/T_1-1/T_2)}$ at $T_{LD} =$	0° 50° C					
$1/T = A + B(\ln R) + C(\ln R)^3$						
T: temperature in Kelvin						
R: resistance at T in Ohm						



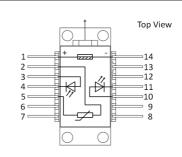
Revision 0.91

SINGLE FREQUENCY LASER DIODES Distributed Feedback Laser

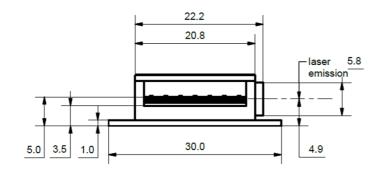


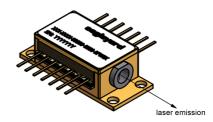
Pin Assignment

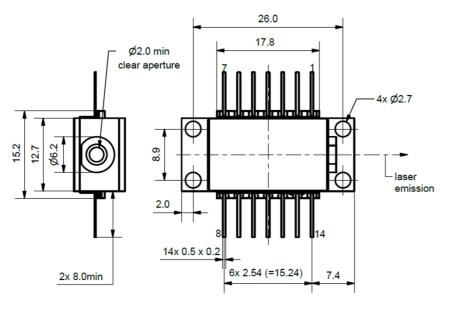
1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)		
2	Thermistor	13	Case		
3	Photodiode (Anode)	12	not connected		
4	Photodiode (Cathode)	11	Laser Diode (Cathode)		
5	Thermistor	10	Laser Diode (Anode)		
6	not connected	9	not connected		
7	not connected	8	not connected		
Pins are isolated from case unless noted otherwise.					



Package Drawings







Caution. Excessive mechanical stress on the package can lead to a damage of the laser.

See <u>instruction manual</u> on www.eagleyard.com

AIZ-20-1029-0928



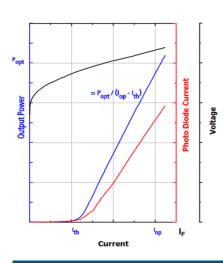
Revision 0.91

SINGLE FREQUENCY LASER DIODES Distributed Feedback Laser

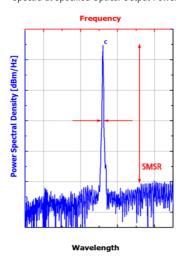


Typical Measurement Results

Output Power vs. Current



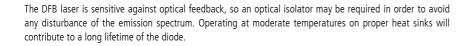
Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.



Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

